

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Enhanced power dissipation capability of 940 mW
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- LED driver
- Power management
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V_{GS}	gate-source voltage			-8	-	8	٧
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	3.4	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 2.8 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	63	73	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



20 V, N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMV65UNE	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV65UNE	%GJ

[1] % = placeholder for manufacturing site code

20 V, N-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	3.4	Α
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	2.8	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	1.8	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	11	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	490	mW
			[1]	-	940	mW
		T _{sp} = 25 °C		-	6.25	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode		'		'	-1
I _S	source current	T _{amb} = 25 °C	[1]	-	0.9	Α

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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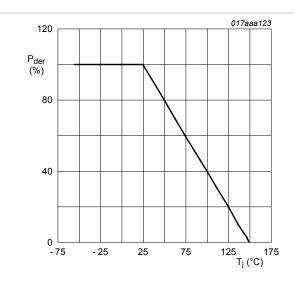


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

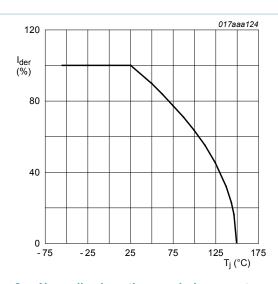


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

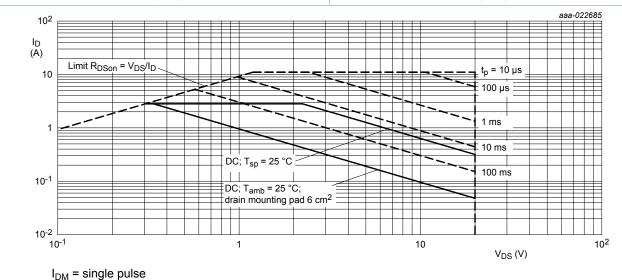


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	221	254	K/W
from ju ambier	from junction to		<u>[2]</u>	-	116	133	K/W
	ambient	in free air; t ≤ 5 s	<u>[2]</u>	-	83	95	K/W

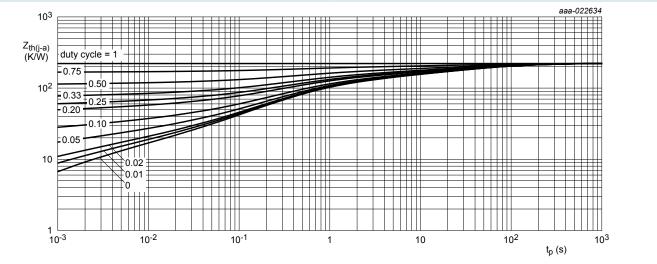
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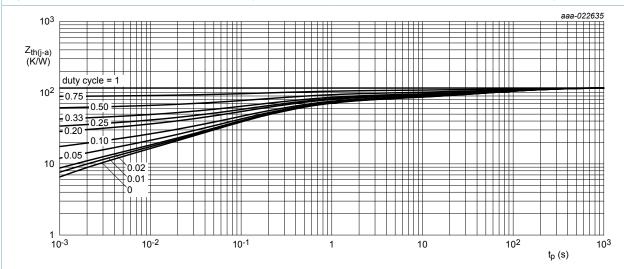
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	17	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.45	0.7	1	V
I _{DSS}	drain leakage current	V _{DS} = 20 V; V _{GS} = 0 V	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-5	μA
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 2.8 \text{ A}; T_j = 25 \text{ °C}$	-	63	73	mΩ
resistance	V _{GS} = 4.5 V; I _D = 2.8 A; T _j = 150 °C	-	93	108	mΩ	
		$V_{GS} = 2.5 \text{ V}; I_D = 2.4 \text{ A}; T_j = 25 \text{ °C}$	-	71	83	mΩ
		$V_{GS} = 1.8 \text{ V}; I_D = 0.8 \text{ A}; T_j = 25 \text{ °C}$	-	83	94	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$	-	11	-	S
R_G	gate resistance	T _j = 25 °C; f = 1 MHz	-	1.8	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I_{D} = 2.8 A; V_{GS} = 4.5 V;	-	3.8	6	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.3	-	nC
Q_{GD}	gate-drain charge		-	0.9	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	291	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	52	-	pF
C _{rss}	reverse transfer capacitance		-	43	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; I_{D} = 2.8 A; V_{GS} = 4.5 V;	-	8	-	ns
t _r	rise time	$R_{G(ext)}$ = 6 Ω ; T_j = 25 °C	-	23	-	ns
$t_{\text{d(off)}}$	turn-off delay time		-	35	-	ns
t _f	fall time		-	12	-	ns
Source-drai	in diode					,
V _{SD}	source-drain voltage	$I_S = 0.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.7	1.2	V
		1				

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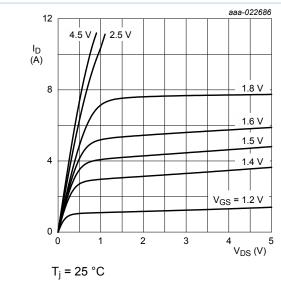


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

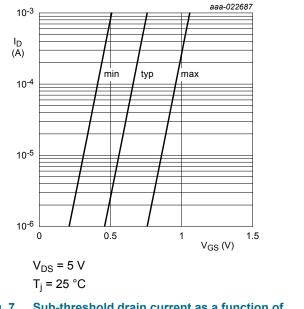


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

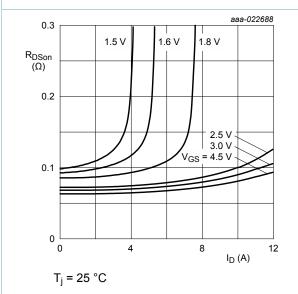


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

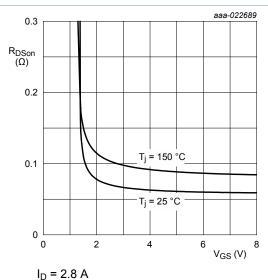


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

20 V, N-channel Trench MOSFET

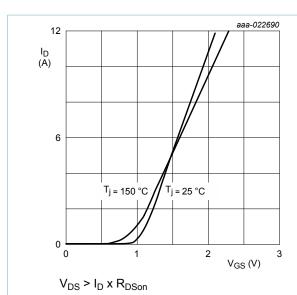


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

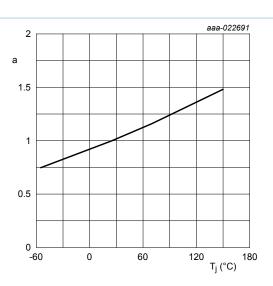


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25\,^{\circ}C)}}$$

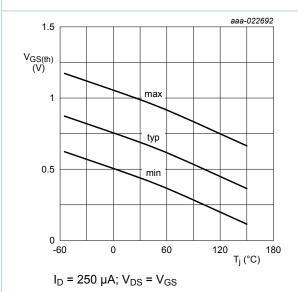


Fig. 12. Gate-source threshold voltage as a function of ambient temperature

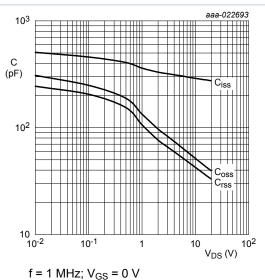
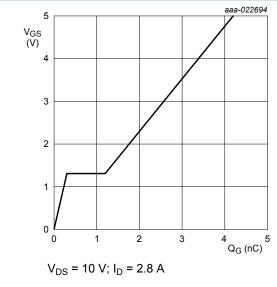


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

V_{DS} -

V_{GS(pl)}

20 V, N-channel Trench MOSFET



V_{GS}(th)
V_{GS}
Q_{GS1} Q_{GS2}
Q_G(tot)
017aaa137

Fig. 15. Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values

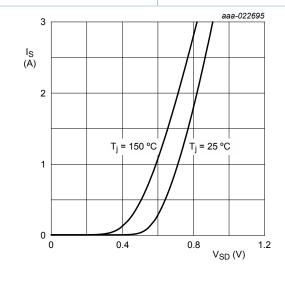
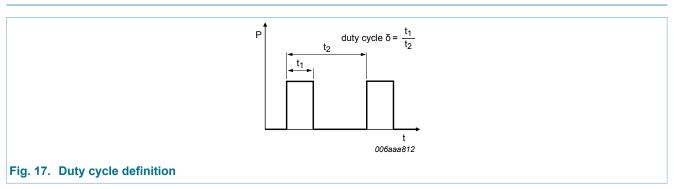


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



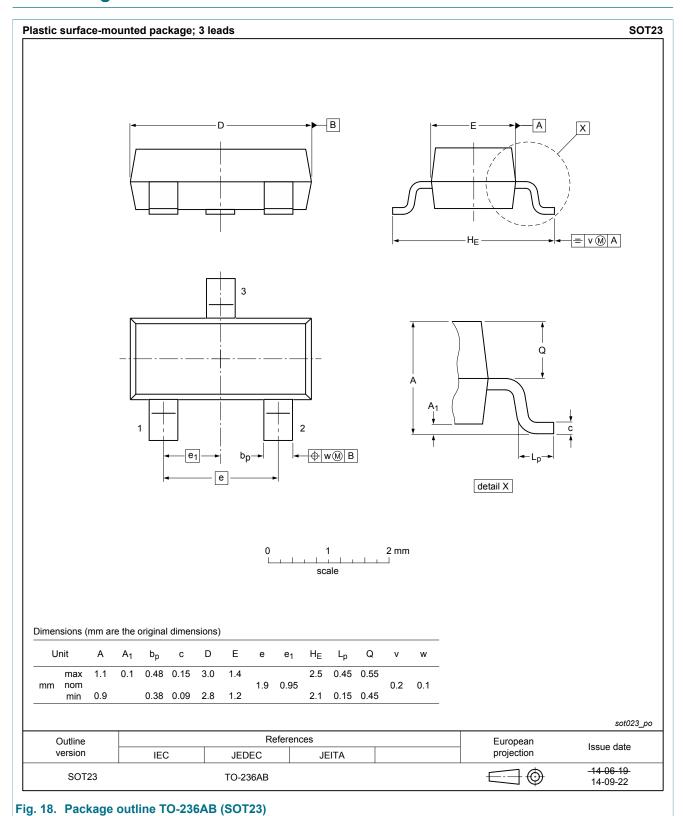
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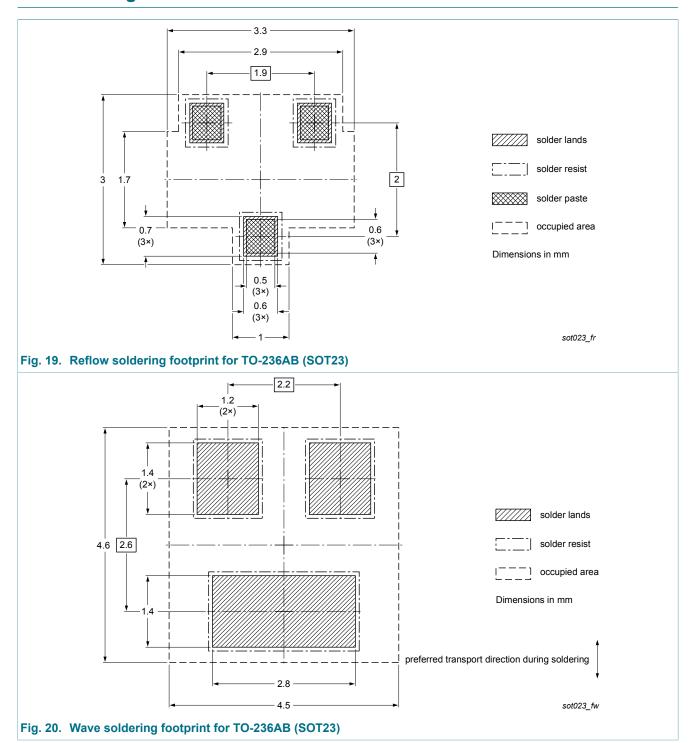
20 V, N-channel Trench MOSFET

12. Package outline



20 V, N-channel Trench MOSFET

13. Soldering



20 V, N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV65UNE v.1	20160422	Product data sheet	-	-

20 V, N-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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20 V, N-channel Trench MOSFET

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20 V, N-channel Trench MOSFET

16. Contents

General description	1
Features and benefits	1
Applications	1
Quick reference data	1
Pinning information	2
Ordering information	2
Marking	2
Limiting values	3
Thermal characteristics	4
Characteristics	6
Test information	9
Package outline	10
Soldering	11
Revision history	12
Legal information	13
Data sheet status	13
Definitions	13
Disclaimers	13
Trademarks	14
	Features and benefits Applications Quick reference data Pinning information Ordering information Marking Limiting values Thermal characteristics Characteristics Test information Package outline Soldering Revision history Legal information Data sheet status Definitions Disclaimers

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